SOI WAFERS - SPECIFICATION SOI-380-2-150

Rev. 1.0 / 09.06.06

**Bonded wafer**
- Growth method: CZ
- Bonding method: Fusion bonding
- Diameter: 100 ± 0.5mm
- Primary Flat Orientation: \(\{110\} \pm 0.5^\circ\)
- Primary Flat Length: 32.5 ± 2.5 mm
- Non-SOI edge area: < 1.5mm (preferably 0mm if not affecting quality)
- Edge Profile: Rounded
- Laser Marking: 380 2 150 SOI [xxx] according to large SEMI STD

**Device Layer**
- Type / Dopant: P / Boron
- Orientation incl. off-orientation: \(\{100\} \pm 0.5^\circ\)
- Resistivity: 1 – 10 Ohmcm
- Thickness: 150 ± 0.7μm

**Buried Oxide**
- Oxide Thickness: 2.00μm ± 3%

**Handle Wafer**
- Type / Dopant: P / Boron
- Orientation incl. off-orientation: \(\{100\} \pm 0.5^\circ\)
- Resistivity: 1 – 10 Ohmcm
- Thickness: 380 ± 5μm
- Back Surface: Polished, without remaining oxide on backside
- Laser Marking: Wafers backside according to PO